

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- Medium Voltage Soft Starts
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages V_{DRM} and V_{RRM} V	Conditions
DCR750F85*	8500	$T_{vj} = -40^{\circ}\text{C}$ to 125°C , $I_{DRM} = I_{RRM} = 200\text{mA}$, $V_{DRM}, V_{RRM} t_p = 10\text{ms}$, $V_{DSM} \& V_{RSM} =$ $V_{DRM} \& V_{RRM} + 100\text{V}$ respectively
DCR750F80	8000	
DCR750F75	7500	
DCR750F70	7000	

Lower voltage grades available.
 *8200V @ -40°C , 8500V @ 0°C

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR750F85

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

KEY PARAMETERS

V_{DRM}	8500V
$I_{T(AV)}$	733A
I_{TSM}	9800A
dV/dt^*	1500V/μs
dI/dt	200A/μs

* Higher dV/dt selections available

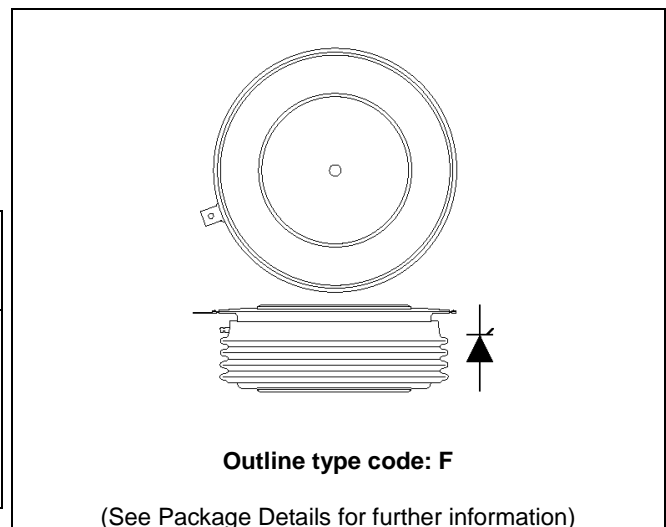


Fig. 1 Package outline

CURRENT RATINGS

$T_{case} = 60^{\circ}\text{C}$ unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Side Cooled				
$I_{T(AV)}$	Mean on-state current	Half wave resistive load	733	A
$I_{T(RMS)}$	RMS value	-	1151	A
I_T	Continuous (direct) on-state current	-	1139	A

SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
I_{TSM}	Surge (non-repetitive) on-state current	10ms half sine, $T_{case} = 125^{\circ}\text{C}$	9.8	kA
I^2t	I^2t for fusing	$V_R = 0$	0.48	MA^2s

THERMAL AND MECHANICAL RATINGS

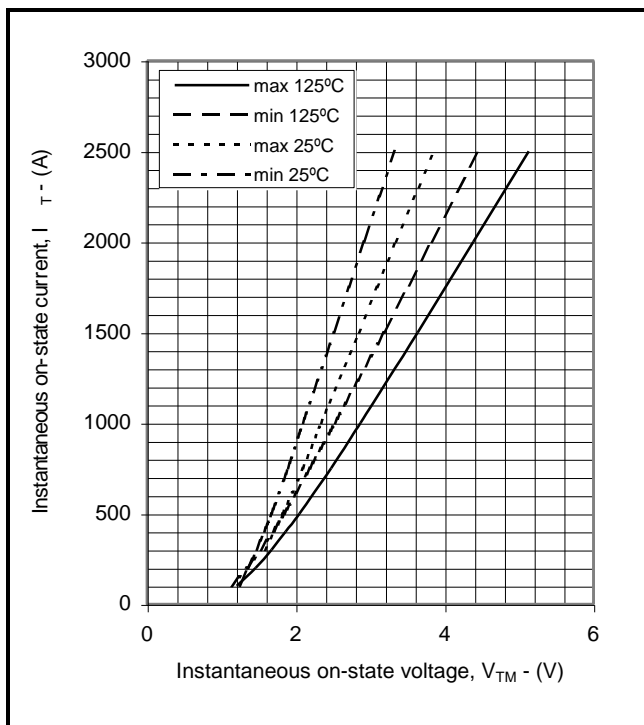
Symbol	Parameter	Test Conditions	Min.	Max.	Units	
$R_{th(j-c)}$	Thermal resistance – junction to case	Double side cooled	DC	-	0.0184	$^{\circ}\text{C/W}$
		Single side cooled	Anode DC	-	0.0333	$^{\circ}\text{C/W}$
			Cathode DC	-	0.0418	$^{\circ}\text{C/W}$
$R_{th(c-h)}$	Thermal resistance – case to heatsink	Clamping force 23 kN (with mounting compound)	Double side	-	0.004	$^{\circ}\text{C/W}$
			Single side	-	0.008	$^{\circ}\text{C/W}$
T_{vj}	Virtual junction temperature	Blocking V_{DRM} / V_{RRM}	-	125	$^{\circ}\text{C}$	
T_{stg}	Storage temperature range		-55	125	$^{\circ}\text{C}$	
F_m	Clamping force		20.0	25.0	kN	

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Conditions	Min.	Max.	Units	
I_{RRM}/I_{DRM}	Peak reverse and off-state current	At V_{RRM}/V_{DRM} , $T_{case} = 125^{\circ}C$	-	200	mA	
dV/dt	Max. linear rate of rise of off-state voltage	To 67% V_{DRM} , $T_j = 125^{\circ}C$, gate open	-	1500	V/ μs	
di/dt	Rate of rise of on-state current	From 67% V_{DRM} to $2x I_{T(AV)}$	Repetitive 50Hz	-	100	A/ μs
		Gate source 30V, 10 Ω , $t_r < 0.5\mu s$, $T_j = 125^{\circ}C$	Non-repetitive	-	200	A/ μs
$V_{T(TO)}$	Threshold voltage – Low level	100A to 500A at $T_{case} = 125^{\circ}C$	-	1.030	V	
	Threshold voltage – High level	500A to 2500A at $T_{case} = 125^{\circ}C$	-	1.30	V	
r_T	On-state slope resistance – Low level	100A to 500A at $T_{case} = 125^{\circ}C$	-	2.06	m Ω	
	On-state slope resistance – High level	500A to 2500A at $T_{case} = 125^{\circ}C$	-	1.542	m Ω	
t_{gd}	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10 Ω $t_r = 0.5\mu s$, $T_j = 25^{\circ}C$	-	3	μs	
t_q	Turn-off time	$T_j = 125^{\circ}C$, $I_{peak} = 1000A$, $t_p = 1000\mu s$, $V_R = 100V$, $di/dt = 5A/\mu s$, $dV_{DR}/dt = 20V/\mu s$ linear to 2500V	-	1200	μs	
I_{RR}	Reverse Recovery current	$I_T = 1000A$, $t_p = 1000\mu s$, $T_j = 125^{\circ}C$, $di/dt = -5A/\mu s$, $V_{Rpeak} = 100V$	95	118	A	
Q_S	Stored charge		3000	4000	μC	
I_L	Latching current	$T_j = 25^{\circ}C$, $V_D = 5V$	-	3	A	
I_H	Holding current	$T_j = 25^{\circ}C$, $R_{G-K} = \infty$, $I_{TM} = 500A$, $I_T = 5A$	-	300	mA	

GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
V _{GT}	Gate trigger voltage	V _{DRM} = 5V, T _{case} = 25°C	1.5	V
V _{GD}	Gate non-trigger voltage	At 50% V _{DRM} , T _{case} = 125°C	0.4	V
I _{GT}	Gate trigger current	V _{DRM} = 5V, T _{case} = 25°C	350	mA
I _{GD}	Gate non-trigger current	At 50% V _{DRM} , T _{case} = 125°C	10	mA

CURVES

Fig.2 Maximum & minimum on-state characteristics
V_{TM} EQUATION

$$V_{TM} = A + B \ln(I_T) + C \cdot I_T + D \cdot \sqrt{I_T}$$

Where A = 0.454245
 B = 0.106933
 C = 0.001271
 D = 0.013218

these values are valid for T_j = 125°C for I_T 100A to 3000A

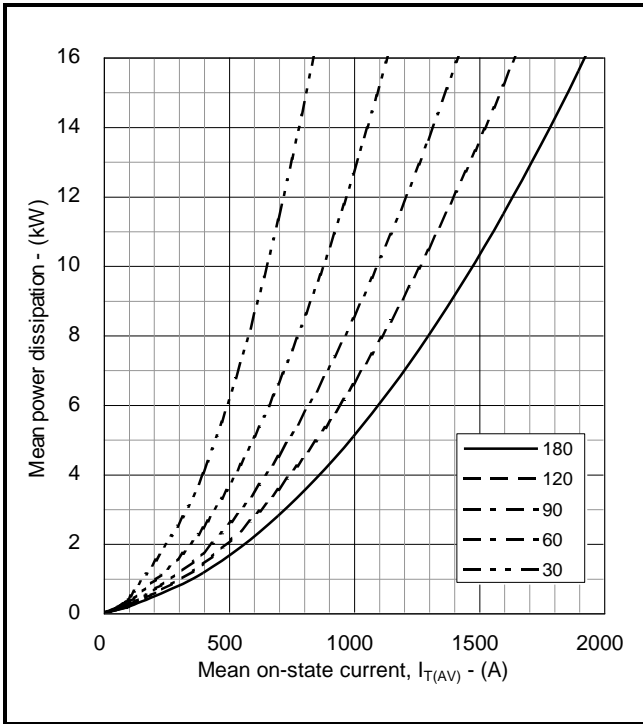


Fig.3 On-state power dissipation – sine wave

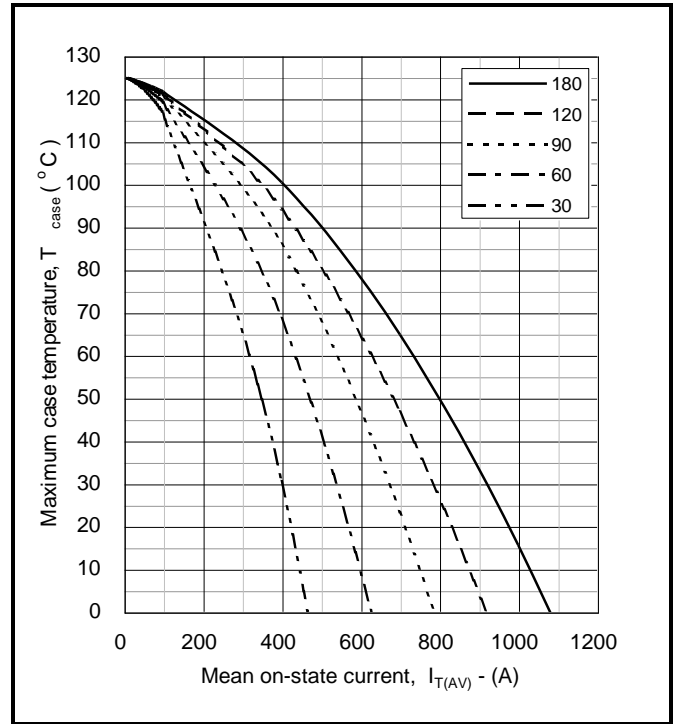


Fig.4 Maximum permissible case temperature, double side cooled – sine wave

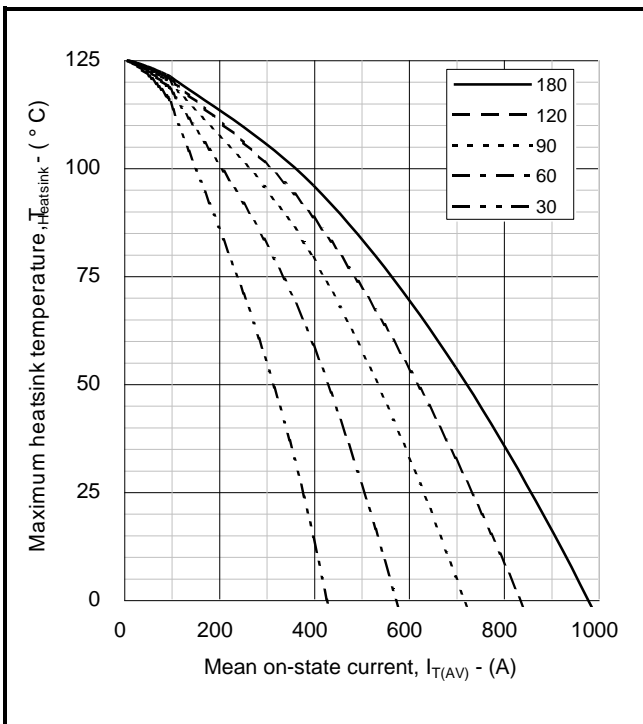


Fig.5 Maximum permissible heatsink temperature, double side cooled – sine wave

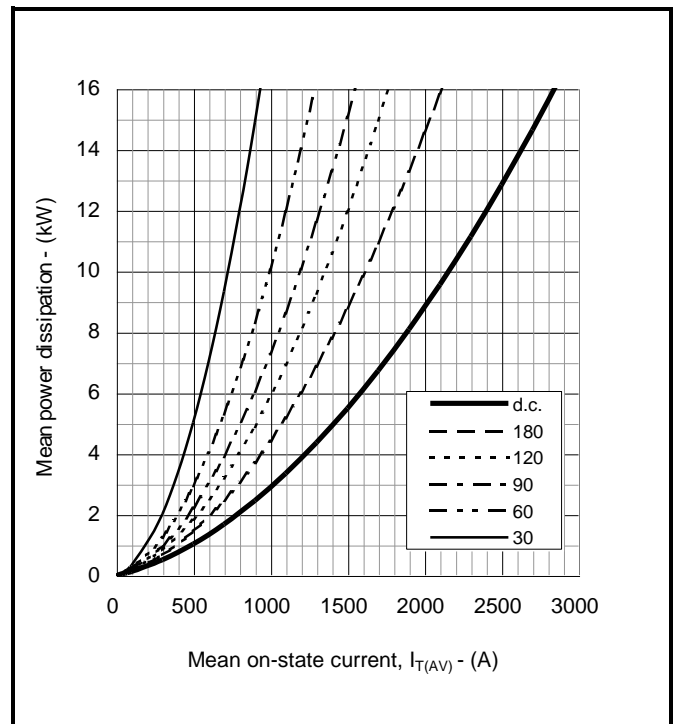


Fig.6 On-state power dissipation – rectangular wave

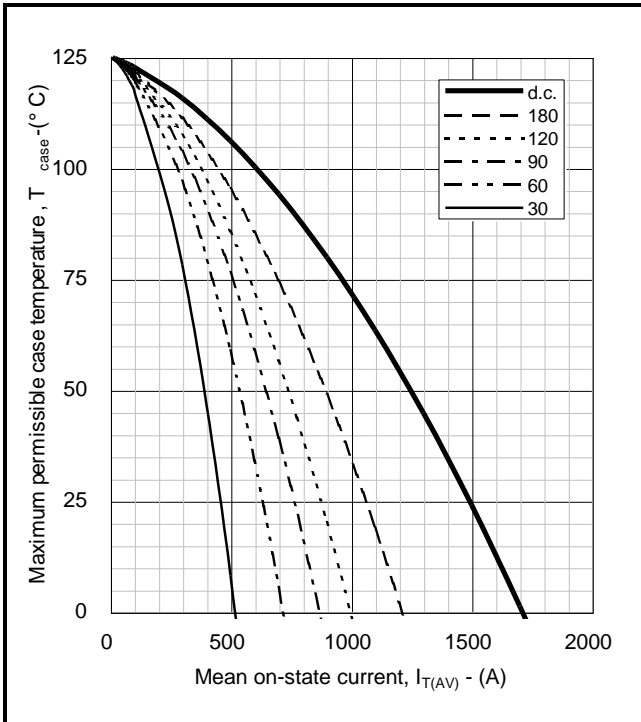


Fig.7 Maximum permissible case temperature, double side cooled – rectangular wave

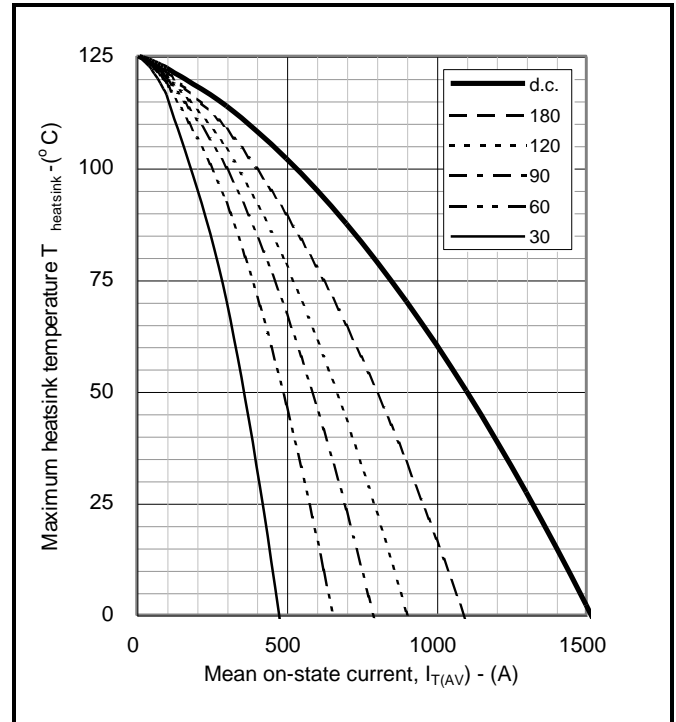


Fig.8 Maximum permissible heatsink temperature, double side cooled – rectangular wave

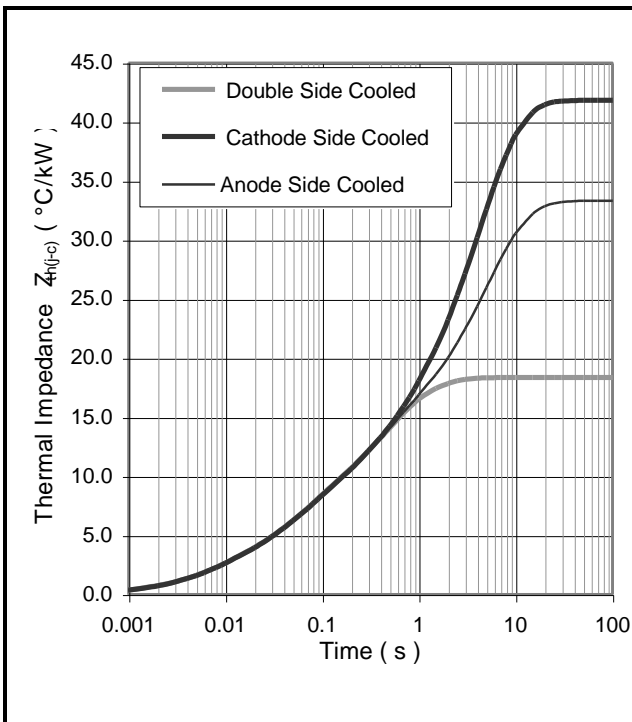


Fig.9 Maximum (limit) transient thermal impedance – junction to case (°C/kW)

		1	2	3	4
Double side cooled	R _i (°C/kW)	7.5608	4.0772	3.8420	2.8671
	T _i (s)	0.6877	0.2537	0.0614	0.0101
Anode side cooled	R _i (°C/kW)	6.7211	4.6219	15.5387	14.8631
	T _i (s)	0.1910	0.0158	5.0011	3.3169
Cathode side cooled	R _i (°C/kW)	11.5564	8.5810	4.7942	8.3643
	T _i (s)	4.2216	6.0269	0.0166	0.2255

$$Z_{th} = \sum_{i=1}^{i=4} [R_i \times (1 - \exp(-T/T_i))]$$

ΔR_{th(j-c)} Conduction

Tables show the increments of thermal resistance R_{th(j-c)} when the device operates at conduction angles other than d.c.

θ°	Double side cooling	
	sine.	rect.
180	3.19	2.14
120	3.72	3.10
90	4.29	3.64
60	4.81	4.23
30	5.22	4.88
15	5.40	5.22

θ°	Anode Side Cooling	
	sine.	rect.
180	2.97	2.03
120	3.43	2.89
90	3.92	3.36
60	4.36	3.87
30	4.69	4.41
15	4.84	4.70

θ°	Cathode Sided Cooling	
	sine.	rect.
180	2.95	2.02
120	3.40	2.87
90	3.88	3.34
60	4.31	3.84
30	4.64	4.37
15	4.79	4.65

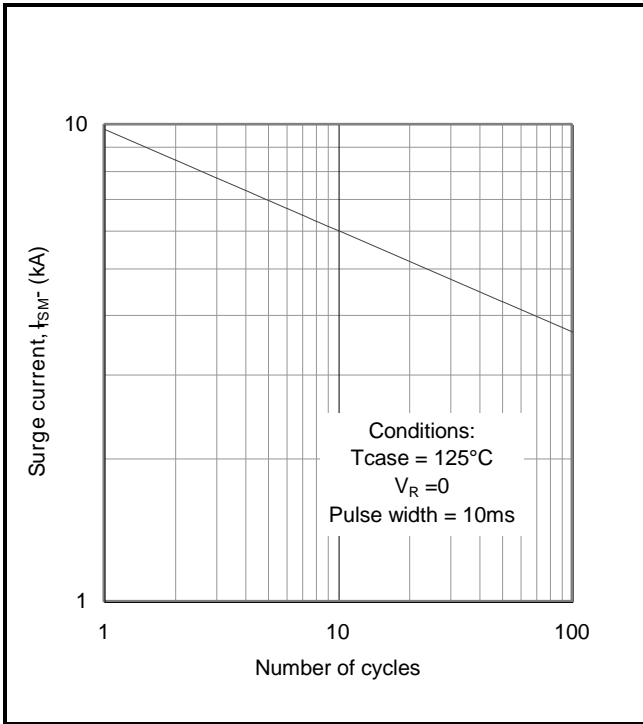


Fig.10 Multi-cycle surge current

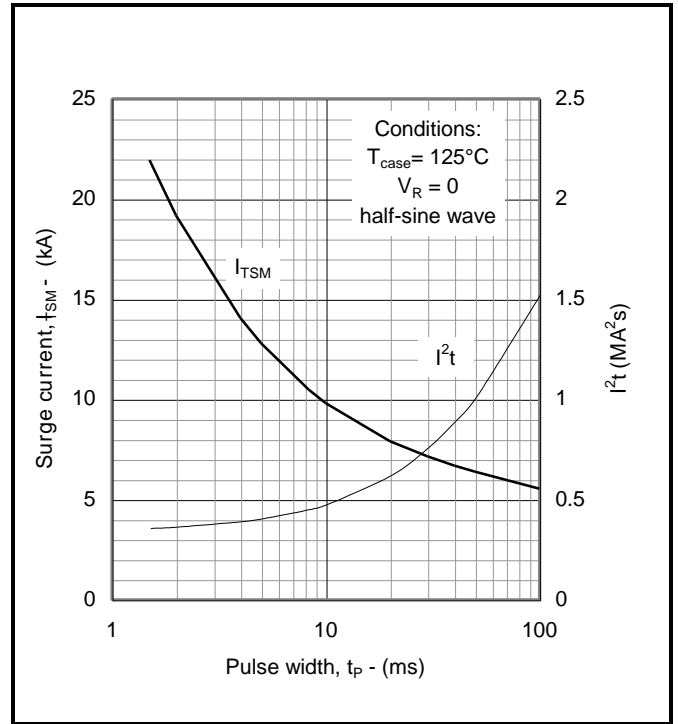


Fig.11 Single-cycle surge current

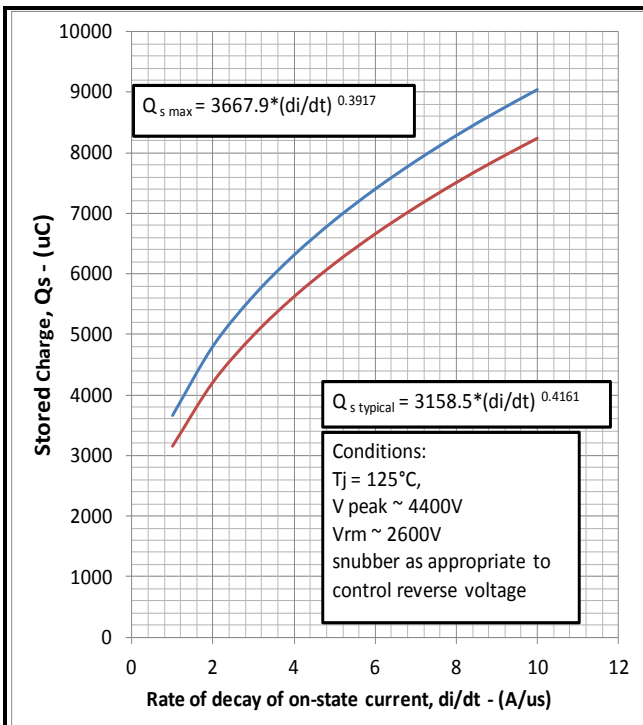


Fig.12 Stored charge

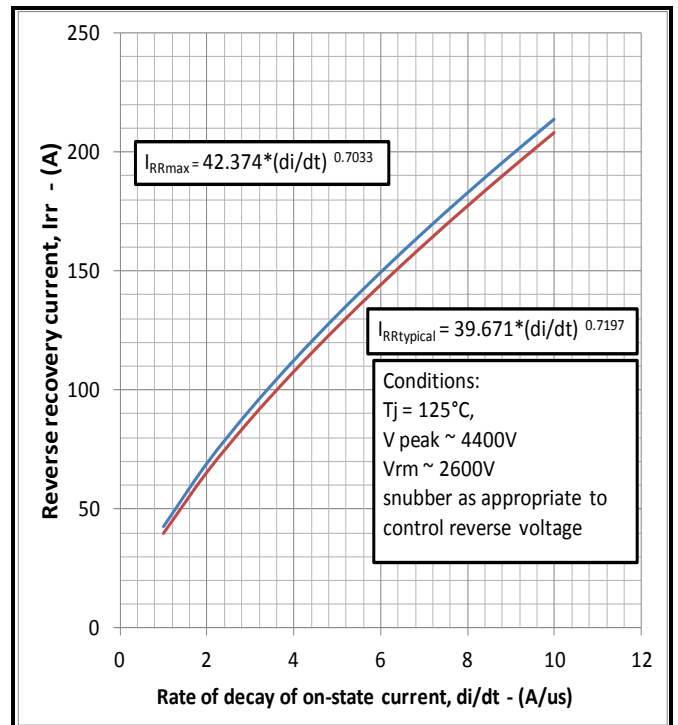


Fig.13 Reverse recovery current

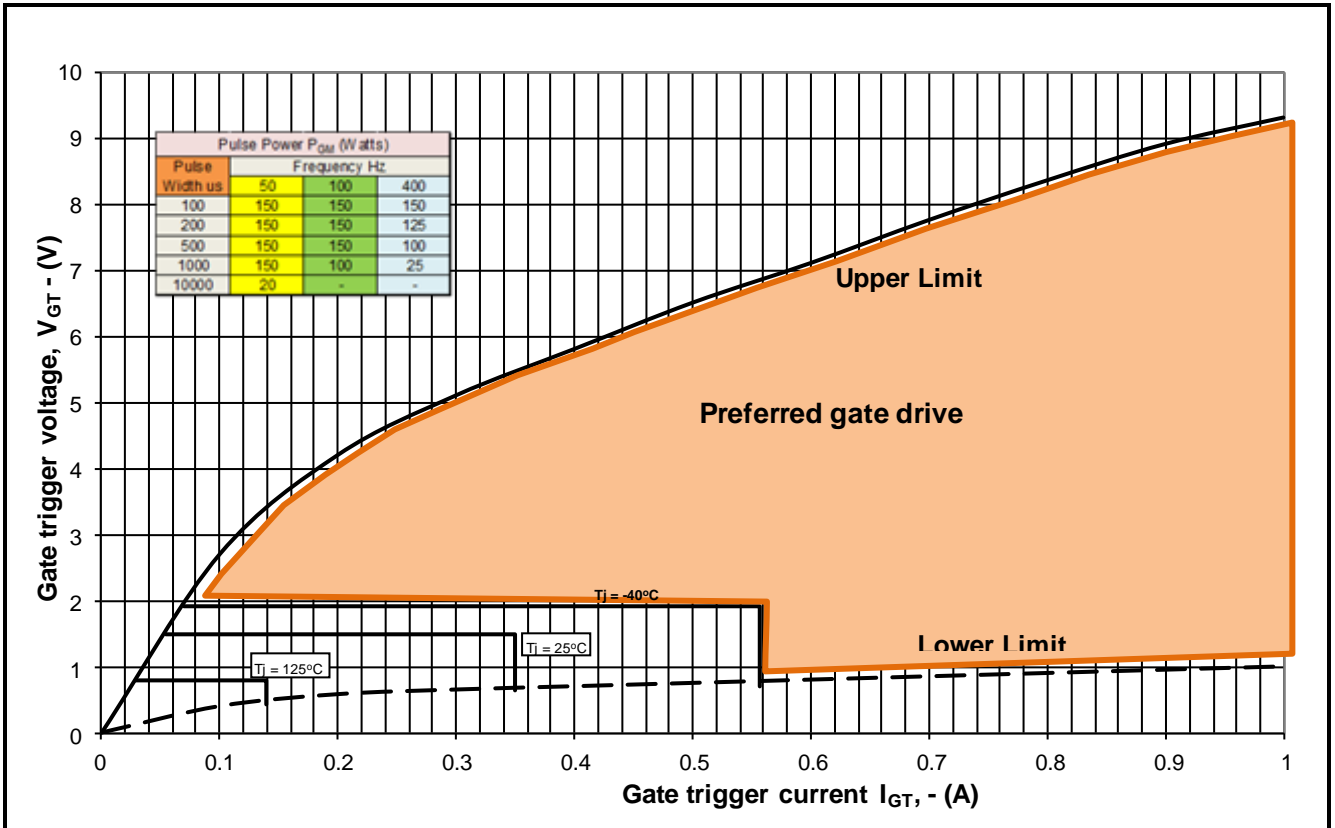


Fig14 Gate Characteristics

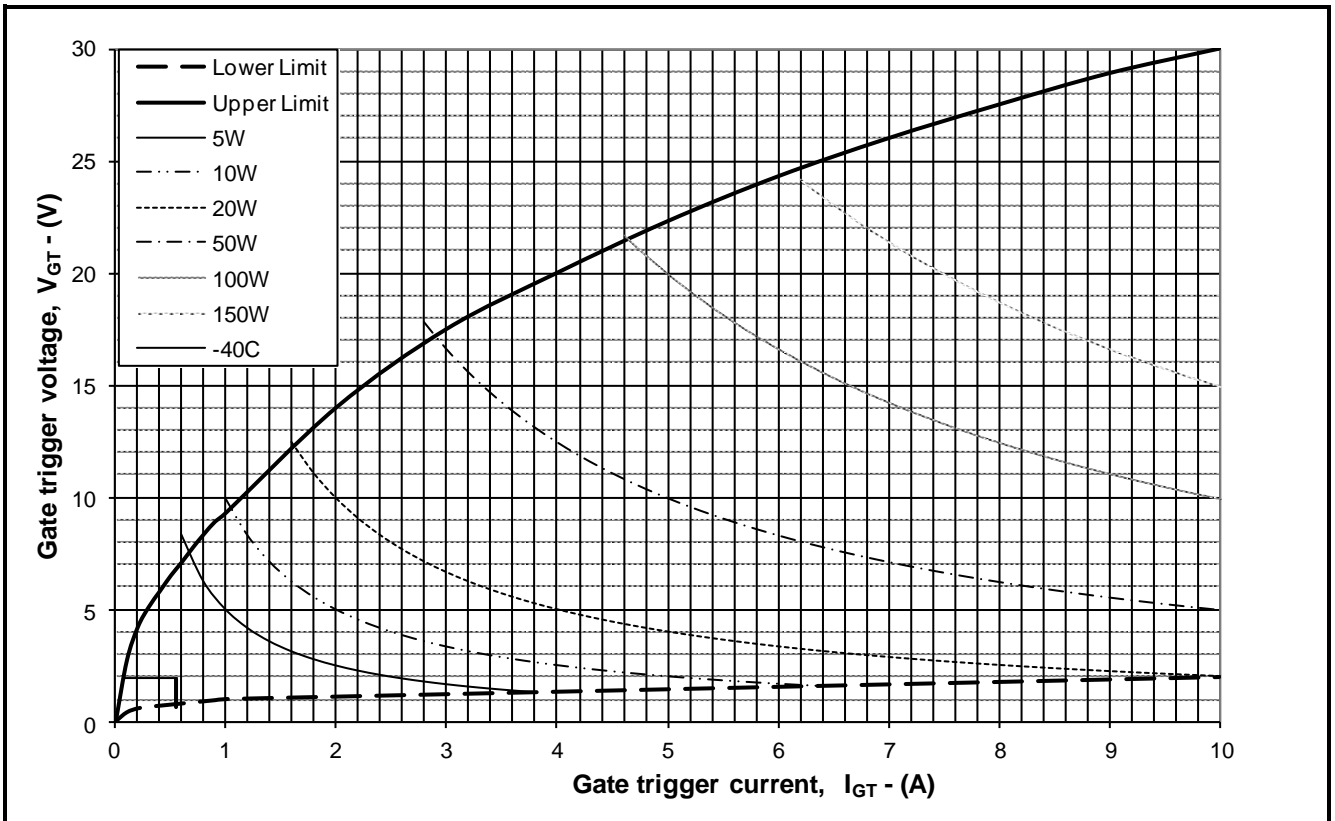


Fig. 15 Gate characteristics

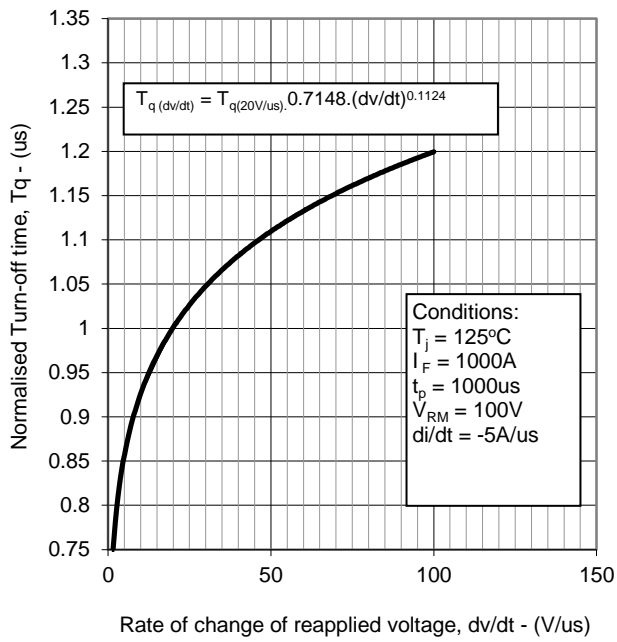
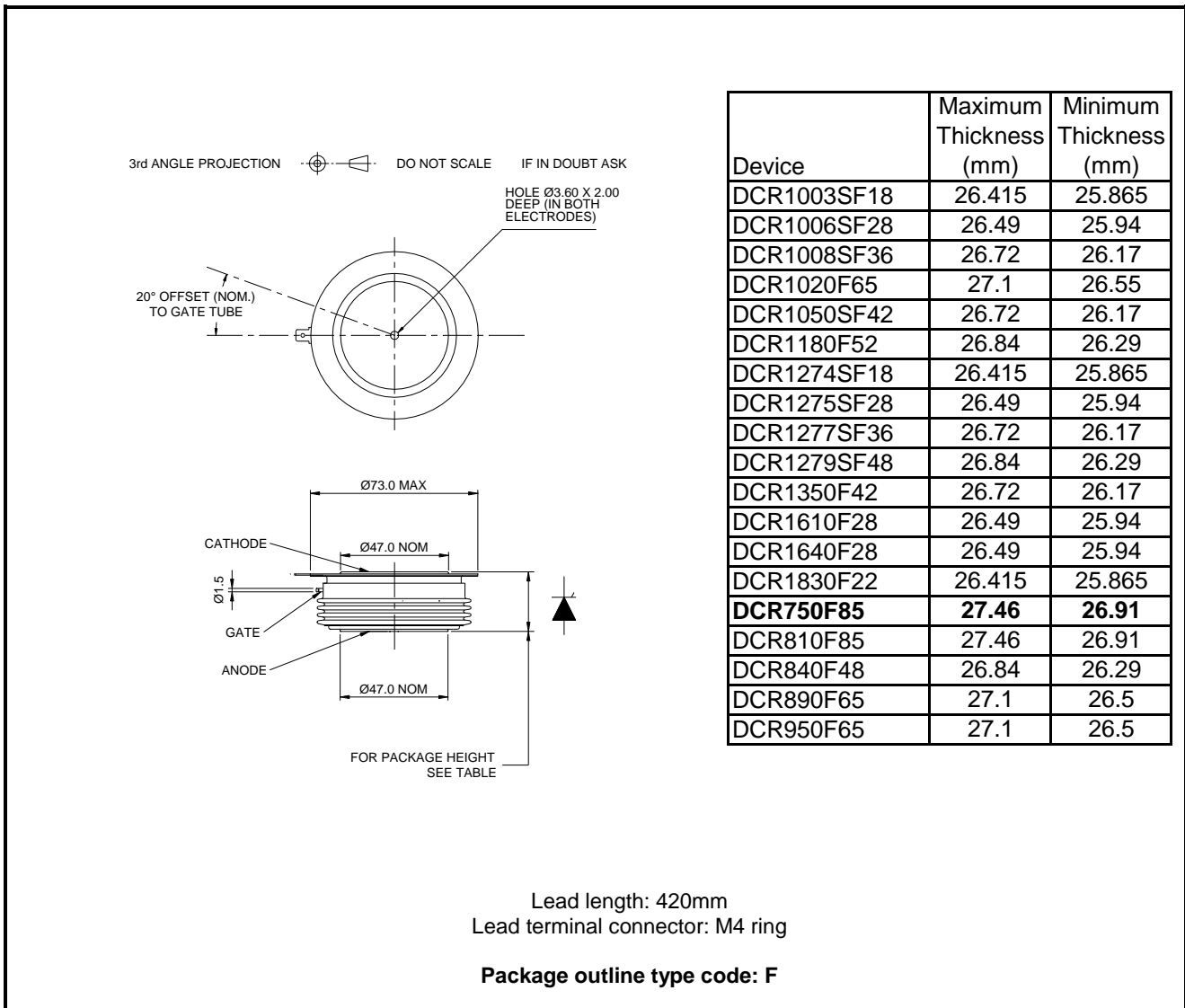


Fig.16 Turn-off time

PACKAGE DETAILS

For further package information, please contact Customer Services. All dimensions in mm, unless stated otherwise. DO NOT SCALE.


Fig.17 Package outline

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